# 2SB0745, 2SB0745A (2SB745, 2SB745A)

## Silicon PNP epitaxial planar type

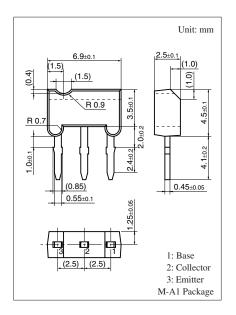
For low-frequency and low-noise amplification

#### ■ Features

- Low noise voltage NV
- High forward current transfer ratio hFE
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SB0745	$V_{CBO}$	-35	V
(Emitter open)	2SB0745A		-55	
Collector-emitter voltage	2SB0745	V <sub>CEO</sub>	-35	V
(Base open)	2SB0745A		-55	
Emitter-base voltage (Coll	$V_{EBO}$	-5	V	
Collector current	$I_C$	-50	mA	
Peak collector current	$I_{CP}$	-200	mA	
Collector power dissipation	P <sub>C</sub>	400	mW	
Junction temperature	$T_{j}$	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	°C	



### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

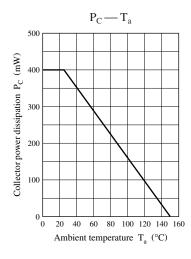
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage	2SB0745	V <sub>CBO</sub>	$I_C = -10 \ \mu A, I_E = 0$	-35			V
(Emitter open)	2SB0745A			-55			
Collector-emitter voltage	2SB0745	V <sub>CEO</sub>	$I_C = -2 \text{ mA}, I_B = 0$	-35			V
(Base open)	2SB0745A			-55			
Emitter-base voltage (Collector open)		$V_{EBO}$	$I_E = -10 \ \mu A, I_C = 0$	-5			V
Base-emitter voltage		$V_{BE}$	$V_{CE} = -1 \text{ V}, I_{C} = -100 \text{ mA}$		- 0.7	-1.0	V
Collector-base cutoff current (Emitter open)		$I_{CBO}$	$V_{CB} = -10 \text{ V}, I_{E} = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)		$I_{CEO}$	$V_{CE} = -10 \text{ V}, I_B = 0$			-1	μΑ
Forward current transfer ratio *		$h_{FE}$	$V_{CE} = -5 \text{ V}, I_{C} = -2 \text{ mA}$	180		700	_
Collector-emitter saturation voltage		V <sub>CE(sat)</sub>	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$			- 0.6	V
Transition frequency		$f_T$	$V_{CB} = -5 \text{ V}, I_E = 2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz
Noise voltage		NV	$V_{CE} = -10 \text{ V}, I_{C} = -1 \text{ mA}, G_{V} = 80 \text{ dB}$ $R_g = 100 \text{ k}\Omega, \text{ Function} = \text{FLAT}$			150	mV

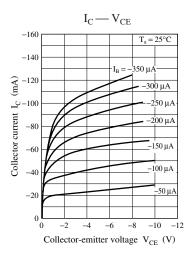
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

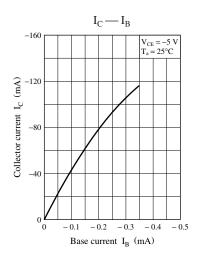
#### 2. \*: Rank classification

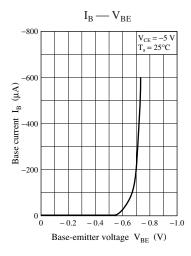
Rank	Q	R	S	
$h_{\mathrm{FE}}$	180 to 360	260 to 520	360 to 700	

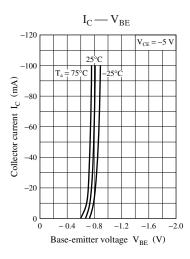
Note) The part numbers in the parenthesis show conventional part number.

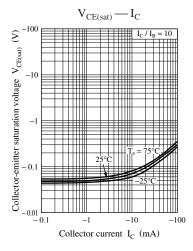


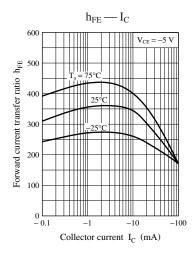


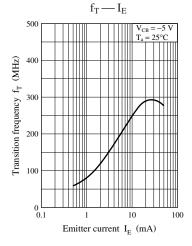


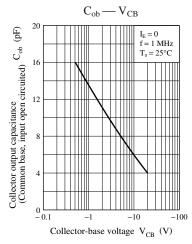


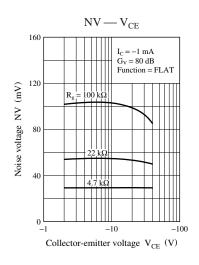


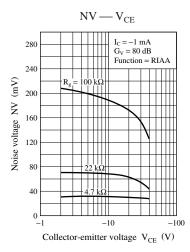


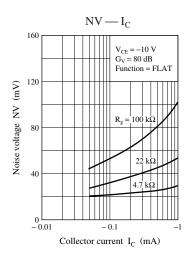


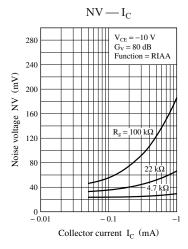


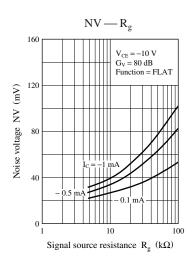


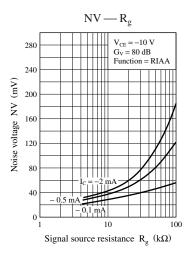












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